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Journal of Crystal Growth 216 (2000) 542–546

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Author index

Aderhold, J., see Stemmer, J. 216 (2000) 15
Ahn, B.-G., see Lee, C.-R. 216 (2000) 62
Aigo, T., see Katsuno, M. 216 (2000) 256
Alexander, H.A., see Palosz, W. 216 (2000) 283
Arnaud d'Avitaya, F., see Bozzo, S. 216 (2000) 171
Asahi, T., see Uchida, M. 216 (2000) 134

Bąk-Misiuk, J., see Szczerbakow, A. 216 (2000) 532
Balestrino, G., see Tagliente, M.A. 216 (2000) 335
Bartram, M.E., W.G. Breiland, L.A. Bruskas and K.P. Killeen, Gas chromatography-mass spectroscopy study of *tert*-butylarsine stability and purification 216 (2000) 33
Berrie, C.L. and S.R. Leone, Observation of monolayer and bilayer period RHEED oscillations during epitaxial growth of Ge on Ge(1 0 0) 216 (2000) 159
Bickermann, M., see Wellmann, P.J. 216 (2000) 263
Billia, B., see Dabo, Y. 216 (2000) 483
Billia, B., see Coriell, S.R. 216 (2000) 495
Blum, R.-P., see Hatami, F. 216 (2000) 26
Bohm, J., E. Chilla, C. Flannery, H.-J. Fröhlich, T. Hauke, R.B. Heimann, M. Hengst and U. Straube, Czochralski growth and characterization of piezoelectric single crystals with langasite structure: $La_3Ga_5SiO_{14}$ (LGS), $La_3Ga_{5.5}Nb_{0.5}O_{14}$ (LGN) and $La_3Ga_{5.5}Ta_{0.5}O_{14}$ (LGT). II. Piezoelectric and elastic properties 216 (2000) 293
Bozzo, S., J.-L. Lazzari, C. Coudreau, A. Ronda, F. Arnaud d'Avitaya, J. Derrien, S. Mesters, B. Hollaender, P. Gergaud and O. Thomas, Chemical vapor deposition of silicon–germanium heterostructures 216 (2000) 171
Braune, K., see Hatami, F. 216 (2000) 26
Breiland, W.G., see Bartram, M.E. 216 (2000) 33
Brown, R.A., see Lipchin, A. 216 (2000) 192
Bruskas, L.A., see Bartram, M.E. 216 (2000) 33
Buligins, L., see Ratnieks, G. 216 (2000) 204

Cai, W.L., see Yao, L.Z. 216 (2000) 147
Carpenter, P., see Su, C.-H. 216 (2000) 104
Chandrasekhar, R., Influence of magnetic field on sodium hexafluorosilicate synthesis 216 (2000) 407
Chen, N.-T., M. Yokoyama and H.-Y. Ueng, Atomic layer epitaxy growth of ZnS_xSe_{1-x} epitaxial layers lattice-matched to Si substrates 216 (2000) 152
Chilla, E., see Bohm, J. 216 (2000) 293
Chilong, C., see Kumar, F.J. 216 (2000) 311
Chitra, J.S.P., see Mahalingam, T. 216 (2000) 304
Chockalingam, M.J., see Mahalingam, T. 216 (2000) 304
Chumachkova, M.M., see Vlasenko, N.A. 216 (2000) 249
Chuman, Y., see Higuchi, M. 216 (2000) 322
Coriell, S.R., see Dabo, Y. 216 (2000) 483
Coriell, S.R., G.B. McFadden, B. Billia, H.N. Thi and Y. Dabo, Electrical pulsing during directional solidification: analysis of transients by Laplace transform 216 (2000) 495
Coudreau, C., see Bozzo, S. 216 (2000) 171
Crausaz, E., see Euvrard, M. 216 (2000) 466
Cui, F.Z., see Feng, Q.L. 216 (2000) 459

Dabo, Y., H.N. Thi, S.R. Coriell, G.B. McFadden, Q. Li and B. Billia, Microsegregation in Peltier interface demarcation 216 (2000) 483
Dabo, Y., see Coriell, S.R. 216 (2000) 495
Dalas, E., see Koutsopoulos, S. 216 (2000) 443
Dalas, E., see Koutsopoulos, S. 216 (2000) 450
Daniels-Race, T., see Li, H. 216 (2000) 527
Danilov, D.A., see Galenko, P.K. 216 (2000) 512
De Caro, L., see Tagliente, M.A. 216 (2000) 335
Deng, P., see Xu, K. 216 (2000) 343
Deng, P., see Yang, P. 216 (2000) 348
Denisova, Z.L., see Vlasenko, N.A. 216 (2000) 249
Derrien, J., see Bozzo, S. 216 (2000) 171
Dynowska, E., see Szczerbakow, A. 216 (2000) 532

Engelbrecht, J.A.A., G.J. Scriven, J.H. Neethling and M.C. Wagener, Crack formation in Zn_3As_2 epilayers grown by MOVPE 216 (2000) 235
Euvrard, M., C. Filiatre and E. Crausaz, A cell to study in situ electrocrystallization of calcium carbonate 216 (2000) 466
Evans, D.A., see Wolfframm, D. 216 (2000) 119

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ELSEVIER

Journal of Crystal Growth 216 (2000) 542–546

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Author index

Aderhold, J., see Stemmer, J. 216 (2000) 15
Ahn, B.-G., see Lee, C.-R. 216 (2000) 62
Aigo, T., see Katsuno, M. 216 (2000) 256
Alexander, H.A., see Palosz, W. 216 (2000) 283
Arnaud d'Avitaya, F., see Bozzo, S. 216 (2000) 171
Asahi, T., see Uchida, M. 216 (2000) 134

Bąk-Misiuk, J., see Szczerbakow, A. 216 (2000) 532
Balestrino, G., see Tagliente, M.A. 216 (2000) 335
Bartram, M.E., W.G. Breiland, L.A. Bruskas and K.P. Killeen, Gas chromatography-mass spectroscopy study of *tert*-butylarsine stability and purification 216 (2000) 33
Berrie, C.L. and S.R. Leone, Observation of monolayer and bilayer period RHEED oscillations during epitaxial growth of Ge on Ge(1 0 0) 216 (2000) 159
Bickermann, M., see Wellmann, P.J. 216 (2000) 263
Billia, B., see Dabo, Y. 216 (2000) 483
Billia, B., see Coriell, S.R. 216 (2000) 495
Blum, R.-P., see Hatami, F. 216 (2000) 26
Bohm, J., E. Chilla, C. Flannery, H.-J. Fröhlich, T. Hauke, R.B. Heimann, M. Hengst and U. Straube, Czochralski growth and characterization of piezoelectric single crystals with langasite structure: $La_3Ga_5SiO_{14}$ (LGS), $La_3Ga_{5.5}Nb_{0.5}O_{14}$ (LGN) and $La_3Ga_{5.5}Ta_{0.5}O_{14}$ (LGT). II. Piezoelectric and elastic properties 216 (2000) 293
Bozzo, S., J.-L. Lazzari, C. Coudreau, A. Ronda, F. Arnaud d'Avitaya, J. Derrien, S. Mesters, B. Hollaender, P. Gergaud and O. Thomas, Chemical vapor deposition of silicon–germanium heterostructures 216 (2000) 171
Braune, K., see Hatami, F. 216 (2000) 26
Breiland, W.G., see Bartram, M.E. 216 (2000) 33
Brown, R.A., see Lipchin, A. 216 (2000) 192
Bruskas, L.A., see Bartram, M.E. 216 (2000) 33
Buligins, L., see Ratnieks, G. 216 (2000) 204

Cai, W.L., see Yao, L.Z. 216 (2000) 147
Carpenter, P., see Su, C.-H. 216 (2000) 104
Chandrasekhar, R., Influence of magnetic field on sodium hexafluorosilicate synthesis 216 (2000) 407
Chen, N.-T., M. Yokoyama and H.-Y. Ueng, Atomic layer epitaxy growth of ZnS_xSe_{1-x} epitaxial layers lattice-matched to Si substrates 216 (2000) 152
Chilla, E., see Bohm, J. 216 (2000) 293
Chilong, C., see Kumar, F.J. 216 (2000) 311
Chitra, J.S.P., see Mahalingam, T. 216 (2000) 304
Chockalingam, M.J., see Mahalingam, T. 216 (2000) 304
Chumachkova, M.M., see Vlasenko, N.A. 216 (2000) 249
Chuman, Y., see Higuchi, M. 216 (2000) 322
Coriell, S.R., see Dabo, Y. 216 (2000) 483
Coriell, S.R., G.B. McFadden, B. Billia, H.N. Thi and Y. Dabo, Electrical pulsing during directional solidification: analysis of transients by Laplace transform 216 (2000) 495
Coudreau, C., see Bozzo, S. 216 (2000) 171
Crausaz, E., see Euvrard, M. 216 (2000) 466
Cui, F.Z., see Feng, Q.L. 216 (2000) 459

Dabo, Y., H.N. Thi, S.R. Coriell, G.B. McFadden, Q. Li and B. Billia, Microsegregation in Peltier interface demarcation 216 (2000) 483
Dabo, Y., see Coriell, S.R. 216 (2000) 495
Dalas, E., see Koutsopoulos, S. 216 (2000) 443
Dalas, E., see Koutsopoulos, S. 216 (2000) 450
Daniels-Race, T., see Li, H. 216 (2000) 527
Danilov, D.A., see Galenko, P.K. 216 (2000) 512
De Caro, L., see Tagliente, M.A. 216 (2000) 335
Deng, P., see Xu, K. 216 (2000) 343
Deng, P., see Yang, P. 216 (2000) 348
Denisova, Z.L., see Vlasenko, N.A. 216 (2000) 249
Derrien, J., see Bozzo, S. 216 (2000) 171
Dynowska, E., see Szczerbakow, A. 216 (2000) 532

Engelbrecht, J.A.A., G.J. Scriven, J.H. Neethling and M.C. Wagener, Crack formation in Zn_3As_2 epilayers grown by MOVPE 216 (2000) 235
Euvrard, M., C. Filiatre and E. Crausaz, A cell to study in situ electrocrystallization of calcium carbonate 216 (2000) 466
Evans, D.A., see Wolfframm, D. 216 (2000) 119

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00509-1

Fan, W., see Li, L. 216 (2000) 538
Fedler, F., see Stemmer, J. 216 (2000) 15
Fehrer, M., see Stemmer, J. 216 (2000) 15
Feng, Q.L., G. Pu, Y. Pei, F.Z. Cui, H.D. Li and T.N. Kim, Polymorph and morphology of calcium carbonate crystals induced by proteins extracted from mollusk shell 216 (2000) 459
Filiatre, C., see Euvrard, M. 216 (2000) 466
Flannery, C., see Bohm, J. 216 (2000) 293
Fröhlich, H.-J., see Bohm, J. 216 (2000) 293
Fu, Q., see Li, L. 216 (2000) 538
Fujimoto, T., see Katsuno, M. 216 (2000) 256

Gałązka, Z. and H. Wilke, Influence of Marangoni convection on the flow pattern in the melt during growth of $Y_3Al_5O_{12}$ single crystals by the Czochralski method 216 (2000) 389
Galenko, P.K. and D.A. Danilov, Selection of the dynamically stable regime of rapid solidification front motion in an isothermal binary alloy 216 (2000) 512
Gay, B.P., see Zheng, H.Q. 216 (2000) 51
Ge, W., see Lu, L. 216 (2000) 141
Gergaud, P., see Bozzo, S. 216 (2000) 171
Ghali, M., see Szczerbakow, A. 216 (2000) 532
Godlewski, M., see Szczerbakow, A. 216 (2000) 532
Golyshev, V.D., M.A. Gonik, V.B. Tsvetovsky, Ya.V. Vasilev and V.N. Shlegel, Determination of supercooling in the presence of macrosteps on the growing facet of BGO 216 (2000) 428
Gonik, M.A., see Golyshev, V.D. 216 (2000) 428
Grasza, K., see Palosz, W. 216 (2000) 283
Graul, J., see Stemmer, J. 216 (2000) 15
Guergouri, K., E. Teyar and R. Triboulet, Study of the effect of polarity and of dislocations on the electrical and optoelectronic properties of p-type $Cd_{0.96}Zn_{0.04}Te$ 216 (2000) 127

Hasan, M.-A., see Li, H. 216 (2000) 527
Hatami, F., U. Müller, H. Kissel, K. Braune, R.-P. Blum, S. Rogaschewski, H. Niehus, H. Kirmse, W. Neumann, M. Schmidbauer, R. Köhler and W.T. Masselink, Planar ordering of InP quantum dots on (100)$In_{0.48}Ga_{0.52}P$ 216 (2000) 26
Hauke, T., see Bohm, J. 216 (2000) 293
He, J. and S. Kou, LEC growth of In-doped GaAs with bottom solid feeding 216 (2000) 21
Heimann, R.B., see Bohm, J. 216 (2000) 293
Hengst, M., see Bohm, J. 216 (2000) 293
Higuchi, M., K. Kodaira and S. Nakayama, Nonstoichiometry in apatite-type neodymium silicate single crystals 216 (2000) 317
Higuchi, M., Y. Chuman, T. Kitagawa and K. Kodaira, Growth of β_{II}-Li_3VO_4 single crystals by the heater-in-zone zone-melting method using a traveling solvent of $LiVO_3$ 216 (2000) 322
Hiroyama, Y., see Wang, D. 216 (2000) 44
Hofmann, D., see Wellmann, P.J. 216 (2000) 263
Hollaender, B., see Bozzo, S. 216 (2000) 171
Hommel, D., see Stemmer, J. 216 (2000) 15
Hommet, J., see Rey, S. 216 (2000) 225
Hong, S., see Li, L. 216 (2000) 538

Ichikawa, M., see Wang, D. 216 (2000) 44
Imaishi, N., see Jing, C.J. 216 (2000) 372
Ivanov, S.V., see Sorokin, V.S. 216 (2000) 97
Ivanov, V.Yu., see Szczerbakow, A. 216 (2000) 532

Jayachandran, M., see Mahalingam, T. 216 (2000) 304
Jeong, H.M., see Ryu, Y.R. 216 (2000) 326
Jeong, H.M., see Ryu, Y.R. 216 (2000) 330
Jing, C.J., N. Imaishi, T. Sato and Y. Miyazawa, Three-dimensional numerical simulation of oxide melt flow in Czochralski configuration 216 (2000) 372

Kadinski, L., see Wellmann, P.J. 216 (2000) 263
Kanaya, M., see Katsuno, M. 216 (2000) 256
Kato, H., see Kinoshita, K. 216 (2000) 37
Katsuno, M., N. Ohtani, T. Aigo, T. Fujimoto, H. Tsuge, H. Yashiro and M. Kanaya, Structural properties of subgrain boundaries in bulk SiC crystals 216 (2000) 256
Killeen, K.P., see Bartram, M.E. 216 (2000) 33
Kim, T.N., see Feng, Q.L. 216 (2000) 459
Kinoshita, K., H. Kato, S. Matsumoto and S.-i. Yoda, Growth of homogeneous $In_{1-x}Ga_xSb$ crystals by the graded solute concentration method 216 (2000) 37
Kirmse, H., see Hatami, F. 216 (2000) 26
Kishida, S., M. Nakamura and W.Y. Liang, Growth of large $Bi_2Sr_2CaCu_2O_y$ single crystals by a vertical Bridgman method 216 (2000) 220
Kishimoto, D., T. Ogura, A. Yamashiki, T. Nishinaga, S. Naritsuka and H. Sakaki, 2D-nucleation on (111)B micro-facet studied by microprobe-RHEED in GaAs MBE for mesa-structure fabrication 216 (2000) 1
Kissel, H., see Hatami, F. 216 (2000) 26
Kitagawa, T., see Higuchi, M. 216 (2000) 322
Klausing, H., see Stemmer, J. 216 (2000) 15
Kodaira, K., see Higuchi, M. 216 (2000) 317
Kodaira, K., see Higuchi, M. 216 (2000) 322
Köhler, R., see Hatami, F. 216 (2000) 26
Kohno, H. and S. Takeda, Periodic instability in growth of chains of crystalline-silicon nanospheres 216 (2000) 185
Kokh, A.E., N.G. Kononova and P.W. Mokruchnikov, An azimuthal pattern of heat field in β-BaB_2O_4 crystal growth 216 (2000) 359
Kondow, M., see Shi, B.Q. 216 (2000) 80

Kononets, Ya.F., see Vlasenko, N.A. 216 (2000) 245
Kononova, N.G., see Kokh, A.E. 216 (2000) 359
Kopytko, Yu.V., see Vlasenko, N.A. 216 (2000) 245
Kou, S., see He, J. 216 (2000) 21
Koutsopoulos, S. and E. Dalas, Hydroxyapatite crystallization in the presence of serine, tyrosine and hydroxyproline amino acids with polar side groups 216 (2000) 443
Koutsopoulos, S. and E. Dalas, The calcification of fibrin in vitro 216 (2000) 450
Kumar, F.J., L.C. Lim, C. Chilong and M.J. Tan, Morphological aspects of flux grown 0.91PZN-0.09PT crystals 216 (2000) 311
Kutsukake, H., see Miyazaki, N. 216 (2000) 6

Lazzari, J.-L., see Bozzo, S. 216 (2000) 171
Le Normand, F., see Rey, S. 216 (2000) 225
Lee, C.-R., J.-Y. Leem and B.-G. Ahn, The annealing effects of Mg-doped GaN epilayers capped with SiO_2 layers 216 (2000) 62
Leem, J.-Y., see Lee, C.-R. 216 (2000) 62
Lehoczky, S.L., see Su, C.-H. 216 (2000) 104
Leone, S.R., see Berrie, C.L. 216 (2000) 159
Li, H., T. Daniels-Race and M.-A. Hasan, Photoluminescence properties of dense InAs/AlInAs quantum wire arrays 216 (2000) 527
Li, H.D., see Feng, Q.L. 216 (2000) 459
Li, L., H. Rui, A. Lu, W. Fan, S. Hong and Q. Fu, Stereo-open spherulites in high-pressure crystallized poly (ethylene terephthalate) 216 (2000) 538
Li, Q., see Dabo, Y. 216 (2000) 483
Liang, J., see Qi, X. 216 (2000) 363
Liang, W.Y., see Kishida, S. 216 (2000) 220
Lim, L.C., see Kumar, F.J. 216 (2000) 311
Lipchin, A. and R.A. Brown, Hybrid finite-volume/finite-element simulation of heat transfer and melt turbulence in Czochralski crystal growth of silicon 216 (2000) 192
Liu, H.-S., see Wang, M.-C. 216 (2000) 69
Liu, J., see Zhang, H. 216 (2000) 367
Liu, W., see Xu, K. 216 (2000) 343
Liu, Y., see Zhang, H. 216 (2000) 367
Look, D.C., see Ryu, Y.R. 216 (2000) 330
Lu, A., see Li, L. 216 (2000) 538
Lu, L., K.K. Mak, Z.H. Ma, J. Wang, I.K. Sou and W. Ge, DX-like centers in n-type Al-doped $ZnS_{1-x}Te_x$ grown by molecular-beam epitaxy 216 (2000) 141
Lüdge, A., see Ratnieks, G. 216 (2000) 204
Lundager Modsen, H.E., see Sørensen, J.S. 216 (2000) 399
Luo, Z., see Qi, X. 216 (2000) 363

Ma, Z.H., see Lu, L. 216 (2000) 141
Mah, K.W., see Zheng, H.Q. 216 (2000) 51
Mahalingam, T., J.S.P. Chitra, S. Rajendran, M. Jayachandran and M.J. Chockalingam, Galvanostatic deposition and characterization of cuprous oxide thin films 216 (2000) 304
Mak, K.K., see Lu, L. 216 (2000) 141
Maruyama, K., K. Suto and J.-i. Nishizawa, ZnSe horizontal traveling solvent growth using selenium solution 216 (2000) 113
Masselink, W.T., see Hatami, F. 216 (2000) 26
Matsuda, Y., see Uchida, M. 216 (2000) 134
Matsumoto, S., see Kinoshita, K. 216 (2000) 37
McFadden, G.B., see Dabo, Y. 216 (2000) 483
McFadden, G.B., see Coriell, S.R. 216 (2000) 495
Medaglia, P.G., see Tagliente, M.A. 216 (2000) 335
Meltser, B.Ya., see Sorokin, V.S. 216 (2000) 97
Meng, X., see Zhang, H. 216 (2000) 367
Mesters, S., see Bozzo, S. 216 (2000) 171
Miceli, P.F., see Ryu, Y.R. 216 (2000) 326
Mistele, D., see Stemmer, J. 216 (2000) 15
Mitrović, M.M., A.A. Žekić and M.M. Napijalo, Correlation between the crystal size and crystal growth rate of KDP and Rochelle salt crystals 216 (2000) 437
Miyazaki, N., S. Yamamoto and H. Kutsukake, Development of dislocation density analysis code for annealing process of single-crystal ingot 216 (2000) 6
Miyazawa, Y., see Jing, C.J. 216 (2000) 372
Mo, C.M., see Yao, L.Z. 216 (2000) 147
Mokruchnikov, P.W., see Kokh, A.E. 216 (2000) 359
Molina, S.I., see Stemmer, J. 216 (2000) 15
Mühlbauer, A., see Ratnieks, G. 216 (2000) 204
Müller, U., see Hatami, F. 216 (2000) 26
Muiznieks, A., see Ratnieks, G. 216 (2000) 204

Nakamura, M., see Kishida, S. 216 (2000) 220
Nakayama, S., see Higuchi, M. 216 (2000) 317
Napijalo, M.M., see Mitrović, M.M. 216 (2000) 437
Naritsuka, S., see Kishimoto, D. 216 (2000) 1
Neethling, J.H., see Engelbrecht, J.A.A. 216 (2000) 235
Neumann, W., see Hatami, F. 216 (2000) 26
Ng, G.I., see Zheng, H.Q. 216 (2000) 51
Niehus, H., see Hatami, F. 216 (2000) 26
Nishinaga, T., see Kishimoto, D. 216 (2000) 1
Nishizawa, J.-i., see Maruyama, K. 216 (2000) 113
Nusret Bulutcu, A., see Şahin, Ö. 216 (2000) 475

Oda, O., see Uchida, M. 216 (2000) 134
Ogawa, T., see Tsuru, T. 216 (2000) 352
Ogura, T., see Kishimoto, D. 216 (2000) 1
Ohtani, N., see Katsuno, M. 216 (2000) 256

Pacheco, F.J., see Stemmer, J. 216 (2000) 15
Palosz, W., Physical vapor transport of lead telluride 216 (2000) 273
Palosz, W., H.A. Alexander and K. Grasza, Thermochemical model and experimental studies on physical vapor transport of lead telluride-selenide 216 (2000) 283

Pei, Y., see Feng, Q.L. 216 (2000) 459
Plomp, M., W.J.P. van Enckevort and E. Vlieg, Etching and surface termination of $K_2Cr_2O_7$ {001} faces observed using in situ atomic force microscopy 216 (2000) 413
Pu, G., see Feng, Q.L. 216 (2000) 459

Qi, X., Z. Luo and J. Liang, Crystal growth of $La_2(WO_4)_3$ 216 (2000) 363

Radhakrishnan, K., see Zheng, H.Q. 216 (2000) 51
Rajendran, S., see Mahalingam, T. 216 (2000) 304
Raming, G., see Ratnieks, G. 216 (2000) 204
Ratnieks, G., A. Muiznieks, L. Buligins, G. Raming, A. Mühlbauer, A. Lüdge and H. Riemann, Influence of the three dimensionality of the HF electromagnetic field on resistivity variations in Si single crystals during FZ growth 216 (2000) 204
Rey, S., J. Hommet, G. Schmerber and F. Le Normand, Diamond growth on polycrystalline nickel silicides 216 (2000) 225
Riahi, D.N., Effects of a vertical magnetic field on chimney convection in a mushy layer 216 (2000) 501
Riemann, H., see Ratnieks, G. 216 (2000) 204
Riley, J., see Wolfframm, D. 216 (2000) 119
Rogaschewski, S., see Hatami, F. 216 (2000) 26
Ronda, A., see Bozzo, S. 216 (2000) 171
Rotter, T., see Stemmer, J. 216 (2000) 15
Rui, H., see Li, L. 216 (2000) 538
Ryu, Y.R., S. Zhu, J.M. Wrobel, H.M. Jeong, P.F. Miceli and H.W. White, Comparative study of textured and epitaxial ZnO films 216 (2000) 326
Ryu, Y.R., S. Zhu, D.C. Look, J.M. Wrobel, H.M. Jeong and H.W. White, Synthesis of p-type ZnO films 216 (2000) 330

Sabharwal, S.C. and Sangeeta, Investigations on cracking in $CdWO_4$ crystals 216 (2000) 535
Sacchetti, A., see Tagliente, M.A. 216 (2000) 335
Şahin, Ö., P. Sayan and A. Nusret Bulutcu, Application of genetic algorithm for determination of mass transfer coefficients 216 (2000) 475
Sakaki, H., see Kishimoto, D. 216 (2000) 1
Sanchez, A.M., see Stemmer, J. 216 (2000) 15
Sangeeta, see Sabharwal, S.C. 216 (2000) 535
Sato, K., see Uchida, M. 216 (2000) 134
Sato, T., see Jing, C.J. 216 (2000) 372
Sayan, P., see Şahin, Ö. 216 (2000) 475
Schmerber, G., see Rey, S. 216 (2000) 225
Schmidbauer, M., see Hatami, F. 216 (2000) 26
Scriven, G.J., see Engelbrecht, J.A.A. 216 (2000) 235
Selder, M., see Wellmann, P.J. 216 (2000) 263
Semchinova, O., see Stemmer, J. 216 (2000) 15
Semenov, A.N., see Sorokin, V.S. 216 (2000) 97
Sha, Y.-G., see Su, C.-H. 216 (2000) 104
Shao, Z., see Zhang, H. 216 (2000) 367
Shi, B.Q., M. Kondow and C.W. Tu, Chemical beam epitaxy of AlAs using novel group-V precursors 216 (2000) 80
Shi, B.Q. and C.W. Tu, A reaction model for chemical beam epitaxy with triethylgallium and tris(dimethylamino)arsenic 216 (2000) 87
Shlegel, V.N., see Golyshev, V.D. 216 (2000) 428
Smallwood, P.L., M.D. Smith and H.-C. zur Loye, Flux synthesis of alkaline earth palladates 216 (2000) 299
Smith, M.D., see Smallwood, P.L. 216 (2000) 299
Soininen, E., see Vlasenko, N.A. 216 (2000) 245
Sørensen, J.S. and H.E. Lundager Madsen, The influence of magnetism on precipitation of calcium phosphate 216 (2000) 399
Sorokin, S.V., see Sorokin, V.S. 216 (2000) 97
Sorokin, V.S., S.V. Sorokin, A.N. Semenov, B.Ya. Meltser and S.V. Ivanov, Novel approach to the calculation of instability regions in GaInAsSb alloys 216 (2000) 97
Sou, I.K., see Lu, L. 216 (2000) 141
Stemmer, J., F. Fedler, H. Klausing, D. Mistele, T. Rotter, O. Semchinova, J. Aderhold, A.M. Sanchez, F.J. Pacheco, S.I. Molina, M. Fehrer, D. Hommel and J. Graul, High temperature AlN intermediate layer in GaN grown by molecular beam epitaxy 216 (2000) 15
Straube, U., see Bohm, J. 216 (2000) 293
Straubinger, T.L., see Wellmann, P.J. 216 (2000) 263
Su, C.-H., Y.-G. Sha, M.P. Volz, P. Carpenter and S.L. Lehoczky, Vapor growth and characterization of ZnSeTe solid solutions 216 (2000) 104
Sun, S.-S., see Vlasenko, N.A. 216 (2000) 245
Suto, K., see Maruyama, K. 216 (2000) 113
Świątek, K., see Szczerbakow, A. 216 (2000) 532
Szczerbakow, A., J. Bąk-Misiuk, E. Dynowska, M. Ghali, M. Godlewski, V.Yu. Ivanov and K. Świątek, Sphalerite-type (Cd, Zn)S films by atomic layer epitaxy in the gas flow 216 (2000) 532

Tagliente, M.A., L. De Caro, A. Sacchetti, L. Tapfer, G. Balestrino, P.G. Medaglia, A. Tebano and A. Tucciarone, X-ray characterization of $LiNbO_3$ films grown by pulsed laser deposition on $SrTiO_3$(1 0 0), $NdGaO_3$(1 1 0) and MgO(1 1 1) substrates 216 (2000) 335
Takeda, S., see Kohno, H. 216 (2000) 185
Tamura, M., see Wang, D. 216 (2000) 44
Tan, M.J., see Kumar, F.J. 216 (2000) 311
Tapfer, L., see Tagliente, M.A. 216 (2000) 335
Tasi, M.-S., see Wang, M.-C. 216 (2000) 69
Tebano, A., see Tagliente, M.A. 216 (2000) 335
Teyar, E., see Guergouri, K. 216 (2000) 127
Thi, H.N., see Dabo, Y. 216 (2000) 483
Thi, H.N., see Coriell, S.R. 216 (2000) 495

Thomas, O., see Bozzo, S. 216 (2000) 171
Tian, Y., see Xu, K. 216 (2000) 343
Triboulet, R., see Guergouri, K. 216 (2000) 127
Tsuge, H., see Katsuno, M. 216 (2000) 256
Tsuru, T. and T. Ogawa, Defects in flux and Czochralski grown β-BaB_2O_4 crystals observed by light scattering tomography 216 (2000) 352
Tsvetovsky, V.B., see Golyshev, V.D. 216 (2000) 428
Tu, C.W., see Shi, B.Q. 216 (2000) 80
Tu, C.W., see Shi, B.Q. 216 (2000) 87
Tucciarone, A., see Tagliente, M.A. 216 (2000) 335

Uchida, M., Y. Matsuda, T. Asahi, K. Sato and O. Oda, Stoichiometry control of ZnTe single crystals by the vapor pressure-controlled wafer-annealing method 216 (2000) 134
Ueng, H.-Y., see Chen, N.-T. 216 (2000) 152

Van Enckevort, W.J.P., see Plomp, M. 216 (2000) 413
Vasilev, Ya.V., see Golyshev, V.D. 216 (2000) 428
Veligura, L.I., see Vlasenko, N.A. 216 (2000) 249
Vlasenko, N.A., Ya.F. Kononets, Yu.V. Kopytko, E. Soininen and S.-S. Sun, Temperature dependence of characteristics of SrS:Cu(Ag) thin-film electroluminescent devices beyond room temperature 216 (2000) 245
Vlasenko, N.A., M.M. Chumachkova, Z.L. Denisova and L.I. Veligura, On nature of centers responsible for inherent memory in ZnS:Mn thin-film electroluminescent devices 216 (2000) 249
Vlieg, E., see Plomp, M. 216 (2000) 413
Volz, M.P., see Su, C.-H. 216 (2000) 104

Wagener, M.C., see Engelbrecht, J.A.A. 216 (2000) 235
Wang, C., see Zhang, H. 216 (2000) 367
Wang, D., Y. Hiroyama, M. Tamura, M. Ichikawa and S. Yoshida, Growth of high-quality cubic GaN on Si (0 0 1) coated with ultra-thin flat SiC by plasma-assisted molecular-beam epitaxy 216 (2000) 44
Wang, J., see Lu, L. 216 (2000) 141
Wang, J., see Zhang, H. 216 (2000) 367
Wang, M.-C., N.-C. Wu, M.-S. Tasi and H.-S. Liu, Preparation and characterization of AlN powders in the $AlCl_3$–NH_3–N_2 system 216 (2000) 69
Wellmann, P.J., M. Bickermann, D. Hofmann, L. Kadinski, M. Selder, T.L. Straubinger and A. Winnacker, In situ visualization and analysis of silicon carbide physical vapor transport growth using digital X-ray imaging 216 (2000) 263
Westwood, D.I., see Wolfframm, D. 216 (2000) 119
White, H.W., see Ryu, Y.R. 216 (2000) 326
White, H.W., see Ryu, Y.R. 216 (2000) 330
Wilke, H., see Gałązka, Z. 216 (2000) 389
Winnacker, A., see Wellmann, P.J. 216 (2000) 263
Wolfframm, D., D.A. Evans, D.I. Westwood and J. Riley, A detailed surface phase diagram for ZnSe MBE growth and ZnSe/GaAs(0 0 1) interface studies 216 (2000) 119
Wrobel, J.M., see Ryu, Y.R. 216 (2000) 326
Wrobel, J.M., see Ryu, Y.R. 216 (2000) 330
Wu, N.-C., see Wang, M.-C. 216 (2000) 69

Xu, J., see Xu, K. 216 (2000) 343
Xu, J., see Yang, P. 216 (2000) 348
Xu, K., P. Deng, J. Xu, G. Zhou, W. Liu and Y. Tian, Growth and characterization of $LiGaO_2$ substrate crystal for GaN epitaxy 216 (2000) 343

Yamamoto, S., see Miyazaki, N. 216 (2000) 6
Yamashiki, A., see Kishimoto, D. 216 (2000) 1
Yang, P., P. Deng, J. Xu and Z. Yin, Growth of high-quality single crystal of 30 at% Yb:YAG and its laser performance 216 (2000) 348
Yao, L.Z., C.H. Ye, C.M. Mo, W.L. Cai and L.D. Zhang, Study of crystallization and spectral properties of PbS nanocrystals doped in SiO_2 aerogel matrix 216 (2000) 147
Yashiro, H., see Katsuno, M. 216 (2000) 256
Ye, C.H., see Yao, L.Z. 216 (2000) 147
Yin, Z., see Yang, P. 216 (2000) 348
Yoda, S.-i., see Kinoshita, K. 216 (2000) 37
Yokoyama, M., see Chen, N.-T. 216 (2000) 152
Yoon, S.F., see Zheng, H.Q. 216 (2000) 51
Yoon, S.F., see Zhuang, Q.D. 216 (2000) 57
Yoshida, S., see Wang, D. 216 (2000) 44
Yuan, K.H., see Zhuang, Q.D. 216 (2000) 57

Žekić, A.A., see Mitrović, M.M. 216 (2000) 437
Zhang, H., X. Meng, J. Liu, L. Zhu, C. Wang, Z. Shao, J. Wang and Y. Liu, Growth of lowly Nd doped $GdVO_4$ single crystal and its laser properties 216 (2000) 367
Zhang, L.D., see Yao, L.Z. 216 (2000) 147
Zheng, H.Q., S.F. Yoon, B.P. Gay, K.W. Mah, K. Radhakrishnan and G.I. Ng, Growth optimization of InGaP layers by solid source molecular beam epitaxy for the application of InGaP/$In_{0.2}Ga_{0.8}As$/ GaAs high electron mobility transistor structures 216 (2000) 51
Zheng, H.Q., see Zhuang, Q.D. 216 (2000) 57
Zhou, G., see Xu, K. 216 (2000) 343
Zhu, L., see Zhang, H. 216 (2000) 367
Zhu, S., see Ryu, Y.R. 216 (2000) 326
Zhu, S., see Ryu, Y.R. 216 (2000) 330
Zhuang, Q.D., S.F. Yoon, H.Q. Zheng and K.H. Yuan, Growth of self-organized InAs quantum dots on InP by solid-source molecular beam epitaxy 216 (2000) 57
Zur Loye, H.-C., see Smallwood, P.L. 216 (2000) 299

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Journal of Crystal Growth 216 (2000) 547–548

JOURNAL OF CRYSTAL GROWTH

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Subject index

Apparatus
– for X-ray imaging 263

Computer simulation
– of dislocation density 6
– of floating zone silicon growth 204
– of heat transfer 389
– of spoke pattern 372
– of surface decomposition mechanism 87
Constitutional supercooling
– of floating zone silicon 204
Convection 192, 204, 359, 372, 501

Dendritic growth
– of alloys 512
– of polymers 538
Device characterization
– diodes 127, 141
– electronic materials 97, 304
– heterojunctions 51, 141
– quantum wires and dots 26, 57
Diamond 225
Diffusonal control
– of lead telluride 273
– of lead telluride selenide 283
Diodes, see Device characterization
Dissolution
– of zinc selenide 113

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical 413

Heterojunctions, see Device characterization
Hydrodynamics, see Convection

Kinetics
– of growth 87, 147, 159, 171, 304, 311, 399, 428, 437, 443, 450, 466, 475, 483, 512
– of interface control 51, 119
– of mass transfer 475
– of nucleation 450, 466

Lasers, crystals for
– ytterbium:YAG 348

Melt growth technique
– by Bridgman–Stockbarger method
– – of BSCCO 220
– by Czochralski method
– – of barium borate 352
– – of cadmium tungstate 535
– – of gadolinium vanadate 367
– – of gallium arsenide 21
– – of lanthanum gallium niobium oxide 293
– – of lanthanum gallium silicon oxide 293
– – of lanthanum gallium tantalum oxide 293
– – of lithium gallium oxide 343
– – of silicon 192
– – of YAG 389
– – of ytterbium:YAG 348
– by floating zone method
– – of neodymium silicate 317
– – of titanium vanadate 322
– by slow cooling
– – of lanthanum tungstate 363
– by uniaxial solidification
– – of bismuth antimony 483, 495
– – of indium gallium antimonide 37
– – of zinc telluride 134
– theory of solidification 501
Morphological stability
– of lead zinc titanate 311

Nucleation
– of calcium carbonate 459, 466
– of diamond 225
Numbers
– Marangoni 372, 389
– Rayleigh 372, 501
– Reynolds 389

Phase diagrams
– of zinc selenide 119
Purification of materials
– of tert butylarsine 33

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
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Quantum wires and dots, see Device characterization

Solution growth technique
- by flux method
- - of barium borate 352, 359
- - of calcium palladium oxide 299
- - of lead zinc titanate 311
- - of strontium palladium oxide 299
- by gel method
- - of lead sulphide 147
- by low temperature method
- - of lanthanum tungstate 363
- - of sodium hexafluorosilicate 407
Stefan problem or moving boundary problem
- of Peltier interface demarcation 483, 495
Superlattices, multilayers
- of silicon germanium 171
- of III–V compounds 527
Surface structure
- of potassium bicromate 413

Thin film growth, epitaxy
- by atomic layer epitaxy
- - of strontium sulphide 245
- - of zinc sulphide selenide 152
- by liquid phase epitaxy
- - of gallium indium arsenide antimonide 97
- by metalorganic molecular beam epitaxy
- - of aluminum arsenide 80
- by molecular beam epitaxy
- - of aluminum nitride 15
- - of gallium arsenide 1
- - of gallium nitride 15, 44
- - of germanium 159
- - of indium aluminum arsenide 527
- - of indium arsenide 57, 527
- - of indium gallium phosphide 51
- - of indium phosphide 26, 57, 527
- - of silicon carbide 44
- - of silicon germanium 171
- - of zinc sulphide telluride 141
- by vapor phase epitaxy
- - through chemical vapor deposition
- - - of silicon germanium 171
- - - theory of simultaneous etching and growth 98
- - through metalorganic chemical vapor deposition
- - - of cadmium zinc sulphide 532
- - - of gallium indium arsenide antimonide 97
- - - of gallium nitride 62
- - - of zinc arsenide 235

Vapor growth technique
- by chemical transport
- - of aluminum nitride 69
- by evaporation and condensation
- - of lead telluride 273
- - of zinc selenide telluride 104
- - of zinc sulphide 249
- by physical vapor transport
- - of silicon carbide 256
- by pulsed laser deposition
- - of lithium niobate 335
- - of zinc oxide 326, 330
- by sublimation
- - of silicon carbide 256

Whisker growth
- of silicon 185